Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	M16C/60
Core Size	16-Bit
Speed	24MHz
Connectivity	I²C, IEBus, UART/USART
Peripherals	DMA, WDT
Number of I/O	85
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	10K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-BQFP
Supplier Device Package	100-QFP (14x20)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/m30620fcpfp-u5c

Table 1.7 Product List (4) (V version (M16C/62PT)) As of Dec. 2005

Type No.	ROM Capacity	RAM Capacity	Package Type[1]	Remarks	
M3062CM6V-XXXFP (P)	48 Kbytes	4 Kbytes	PRQP0100JB-A	Mask ROM version	V Version (High reliability 125°C version)
M3062CM6V-XXXGP (P)			PLQP0100KB-A		
M3062EM6V-XXXGP (P)			PRQP0080JA-A		
M3062CM8V-XXXFP (P)	64 Kbytes	4 Kbytes	PRQP0100JB-A		
M3062CM8V-XXXGP (P)			PLQP0100KB-A		
M3062EM8V-XXXGP (P)			PRQP0080JA-A		
M3062CMAV-XXXFP (P)	96 Kbytes	5 Kbytes	PRQP0100JB-A		
M3062CMAV-XXXGP (P)			PLQP0100KB-A		
M3062EMAV-XXXGP (P)			PRQP0080JA-A		
M3062AMCV-XXXFP (D)	128 Kbytes	10 Kbytes	PRQP0100JB-A		
M3062AMCV-XXXGP (D)			PLQP0100KB-A		
M3062BMCV-XXXGP (P)			PRQP0080JA-A		
M3062AFCVFP (D)	128K+4 Kbytes	10 Kbytes	PRQP0100JB-A	Flash memory version [2]	
M3062AFCVGP (D)			PLQP0100KB-A		
M3062BFCVGP (P)			PRQP0080JA-A		
M3062JFHVFP (P)	384K+4 Kbytes	31 Kbytes	PRQP0100JB-A		
M3062JFHVGP (P)			PLQP0100KB-A		

(D): Under development
(P): Under planning
NOTES:

1. The old package type numbers of each package type are as follows.
   PLQP0128KB-A : 128P6Q-A,
   PRQP0100JB-A : 100P6S-A,
   PLQP0100KB-A : 100P6Q-A,
   PRQP0080JA-A : 80P6S-A
2. In the flash memory version, there is 4K bytes area (block A).

Table 1.14 Pin Characteristics for 100-Pin Package (2)

Pin No.		Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
FP	GP							
51	49		P4_3					A19
52	50		P4_2					A18
53	51		P4_1					A17
54	52		P4_0					A16
55	53		P3_7					A15
56	54		P3_6					A14
57	55		P3_5					A13
58	56		P3_4					A12
59	57		P3_3					A11
60	58		P3_2					A10
61	59		P3_1					A9
62	60	VCC2						
63	61		P3_0					A8(/-/D7)
64	62	VSS						
65	63		P2_7				AN2_7	A7(/D7/D6)
66	64		P2_6				AN2_6	A6(/D6/D5)
67	65		P2_5				AN2_5	A5(/D5/D4)
68	66		P2_4				AN2_4	A4(/D4/D3)
69	67		P2_3				AN2_3	A3(/D3/D2)
70	68		P2_2				AN2_2	A2(/D2/D1)
71	69		P2_1				AN2_1	A1(/D1/D0)
72	70		P2_0				AN2_0	A0(/D0/-)
73	71		P1_7	$\overline{\text{INT5}}$				D15
74	72		P1_6	$\overline{\text{INT4}}$				D14
75	73		P1_5	$\overline{\text{INT3}}$				D13
76	74		P1_4					D12
77	75		P1_3					D11
78	76		P1_2					D10
79	77		P1_1					D9
80	78		P1_0					D8
81	79		P0_7				AN0_7	D7
82	80		P0_6				AN0_6	D6
83	81		P0_5				AN0_5	D5
84	82		P0_4				AN0_4	D4
85	83		P0_3				AN0_3	D3
86	84		P0_2				AN0_2	D2
87	85		P0_1				AN0_1	D1
88	86		P0_0				AN0_0	D0
89	87		P10_7	$\overline{\text{KI3}}$			AN7	
90	88		P10_6	$\overline{\text{KI2}}$			AN6	
91	89		P10_5	$\overline{\text{KI1}}$			AN5	
92	90		P10_4	$\overline{\text{KI0}}$			AN4	
93	91		P10_3				AN3	
94	92		P10_2				AN2	
95	93		P10_1				AN1	
96	94	AVSS						
97	95		P10_0				AN0	
98	96	VREF						
99	97	AVCC						
100	98		P9_7			SIN4	$\overline{\text{ADTRG}}$	

Table 1.16 Pin Characteristics for 80-Pin Package (2)

Pin No.	Control Pin	Port	Interrupt Pin	Timer Pin	UART Pin	Analog Pin	Bus Control Pin
51		P3_0					
52		P2_7				AN2_7	
53		P2_6				AN2_6	
54		P2_5				AN2_5	
55		P2_4				AN2_4	
56		P2_3				AN2_3	
57		P2_2				AN2_2	
58		P2_1				AN2_1	
59		P2_0				AN2_0	
60		P0_7				AN0_7	
61		P0_6				AN0_6	
62		P0_5				AN0_5	
63		P0_4				AN0_4	
64		P0_3				AN0_3	
65		P0_2				AN0_2	
66		P0_1				AN0_1	
67		P0_0				AN0_0	
68		P10_7	$\overline{\text{KI3}}$			AN7	
69		P10_6	$\overline{\text{KI2}}$			AN6	
70		P10_5	$\overline{\text{KI1}}$			AN5	
71		P10_4	$\overline{\text{KI0}}$			AN4	
72		P10_3				AN3	
73		P10_2				AN2	
74		P10_1				AN1	
75	AVSS						
76		P10_0				AN0	
77	VREF						
78	AVCC						
79		P9_7			SIN4	$\overline{\text{ADTRG}}$	
80		P9_6			SOUT4	ANEX1	

Table 1.19 Pin Description (100-pin and 128-pin Version) (3)

Signal Name	Pin Name	I/O Type	Power Supply(1)	Description
Reference voltage input	VREF	I	VCC1	Applies the reference voltage for the A/D converter and D/A converter.
A/D converter	AN0 to AN7, AN0_0 to AN0_7, AN2_0 to AN2_7	I	VCC1	Analog input pins for the A/D converter.
	$\overline{\text{ADTRG}}$	I	VCC1	This is an A/D trigger input pin.
	ANEX0	I/O	VCC1	This is the extended analog input pin for the A/D converter, and is the output in external op-amp connection mode.
	ANEX1	I	VCC1	This is the extended analog input pin for the A/D converter.
D/A converter	DA0, DA1	O	VCC1	This is the output pin for the D/A converter.
I/O port	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7 (2), P13_0 to P13_7 (2)	I/O	VCC2	8-bit I/O ports in CMOS, having a direction register to select an input or output. Each pin is set as an input port or output port. An input port can be set for a pull-up or for no pull-up in 4-bit unit by program.
	P6_0 to P6_7, P7_0 to P7_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7 (2)	I/O	VCC1	8-bit I/O ports having equivalent functions to P0. (however, output of P7_0 and P7_1 for the N-channel open drain output.)
	P8_0 to P8_4, P8_6, P8_7, P14_0, P14_1(2)	I/O	VCC1	I/O ports having equivalent functions to P0.
Input port	P8_5	I	VCC1	Input pin for the $\overline{\text{NMI}}$ interrupt. Pin states can be read by the P8_5 bit in the P8 register.

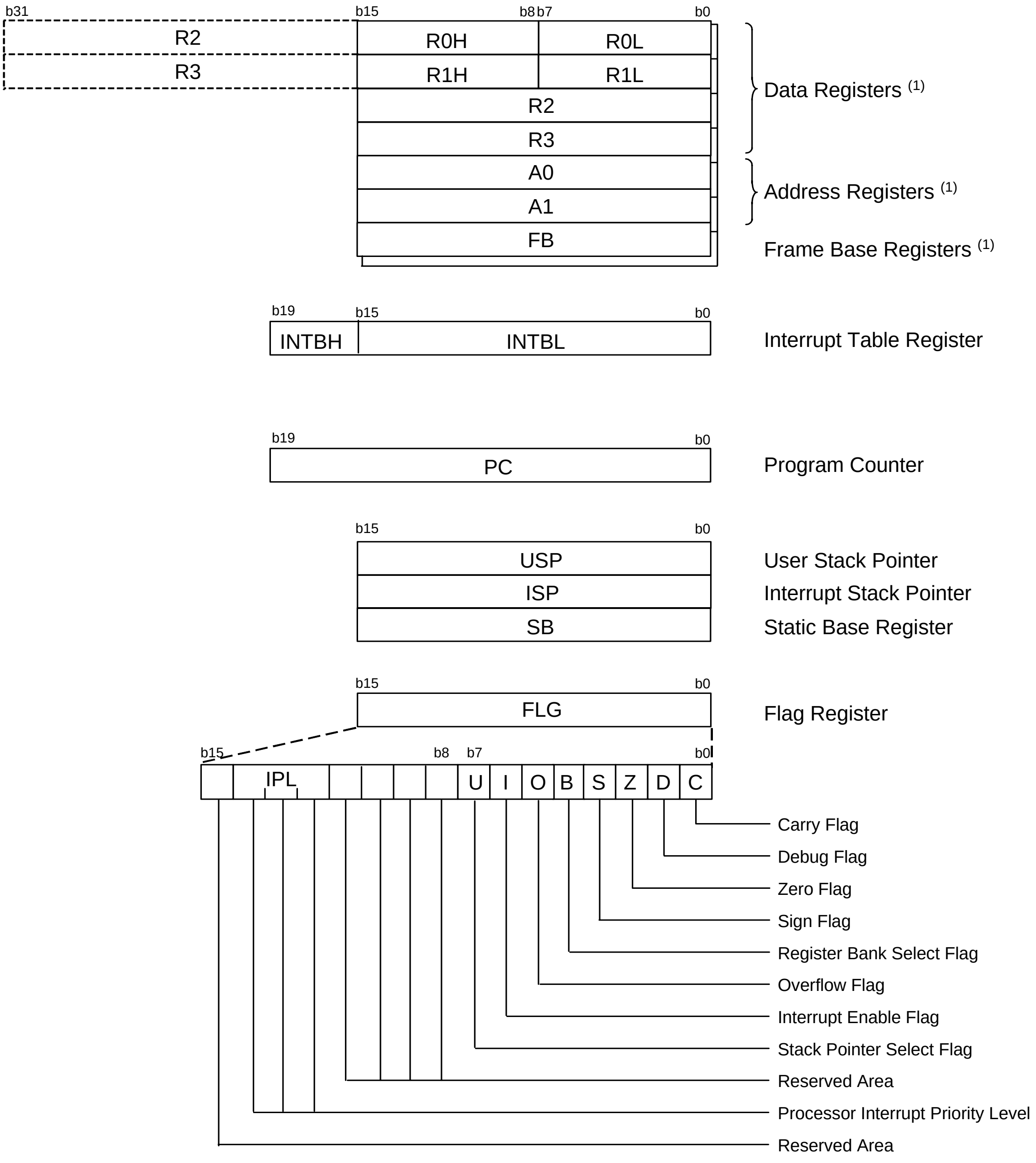
I : Input O : Output I/O : Input and output

NOTES:

1. When use VCC1 > VCC2, contacts due to some points or restrictions to be checked.
2. Ports P11 to P14 in M16C/62P (100-pin version) and M16C/62PT (100-pin version) cannot be used.

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU registers. The CPU has 13 registers. Of these, R0, R1, R2, R3, A0, A1 and FB comprise a register bank. There are two register banks.



NOTES:
1. These registers comprise a register bank. There are two register banks.

Figure 2.1 Central Processing Unit Register

2.1 Data Registers (R0, R1, R2 and R3)

The R0 register consists of 16 bits, and is used mainly for transfers and arithmetic/logic operations. R1 to R3 are the same as R0.

The R0 register can be separated between high (R0H) and low (R0L) for use as two 8-bit data registers.

R1H and R1L are the same as R0H and R0L. Conversely, R2 and R0 can be combined for use as a 32-bit data register (R2R0). R3R1 is the same as R2R0.

5. Electrical Characteristics

5.1 Electrical Characteristics (M16C/62P)

Table 5.1 **Absolute Maximum Ratings**

Symbol	Parameter		Condition	Rated Value	Unit
V_{CC1}, V_{CC2}	Supply Voltage		V_{CC1}=AV_{CC}	−0.3 to 6.5	V
V_{CC2}	Supply Voltage		V_{CC2}	−0.3 to V_{CC1}+0.1	V
AV_{CC}	Analog Supply Voltage		V_{CC1}=AV_{CC}	−0.3 to 6.5	V
V_I	Input Voltage	$\overline{\text{RESET}}$, CNVSS, BYTE, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, VREF, XIN		−0.3 to V_{CC1}+0.3 (1)	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		−0.3 to V_{CC2}+0.3 (1)	V
		P7_0, P7_1		−0.3 to 6.5	V
V_O	Output Voltage	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, XOUT		−0.3 to V_{CC1}+0.3 (1)	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		−0.3 to V_{CC2}+0.3 (1)	V
		P7_0, P7_1		−0.3 to 6.5	V
P_d	Power Dissipation		$-40°C<T_{opr}\leq 85°C$	300	mW
T_{opr}	Operating Ambient Temperature	When the Microcomputer is Operating		−20 to 85 / −40 to 85	°C
		Flash Program Erase		0 to 60	
T_{stg}	Storage Temperature			−65 to 150	°C

NOTES:

1. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.

Table 5.2 Recommended Operating Conditions (1) (1)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
V_{CC1}, V_{CC2}	Supply Voltage ($V_{CC1} \geq V_{CC2}$)		2.7	5.0	5.5	V
AV_{CC}	Analog Supply Voltage			V_{CC1}		V
V_{SS}	Supply Voltage			0		V
AV_{SS}	Analog Supply Voltage			0		V
V_{IH}	HIGH Input Voltage	P3_1 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	0.8V_{CC2}		V_{CC2}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (during single-chip mode)	0.8V_{CC2}		V_{CC2}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (data input during memory expansion and microprocessor mode)	0.5V_{CC2}		V_{CC2}	V
		P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, XIN, $\overline{\text{RESET}}$, CNVSS, BYTE	0.8V_{CC1}		V_{CC1}	V
		P7_0, P7_1	0.8V_{CC1}		6.5	V
V_{IL}	LOW Input Voltage	P3_1 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7	0		0.2V_{CC2}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (during single-chip mode)	0		0.2V_{CC2}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 (data input during memory expansion and microprocessor mode)	0		0.16V_{CC2}	V
		P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1, XIN, $\overline{\text{RESET}}$, CNVSS, BYTE	0		0.2V_{CC}	V
$I_{OH(peak)}$	HIGH Peak Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			–10.0	mA
$I_{OH(avg)}$	HIGH Average Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			–5.0	mA
$I_{OL(peak)}$	LOW Peak Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			10.0	mA
$I_{OL(avg)}$	LOW Average Output Current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1			5.0	mA

NOTES:

1. Referenced to V_{CC1} = V_{CC2} = 2.7 to 5.5V at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified.
2. The Average Output Current is the mean value within 100ms.
3. The total $I_{OL(peak)}$ for ports P0, P1, P2, P8_6, P8_7, P9, P10, P11, P14_0, and P14_1 must be 80mA max. The total $I_{OL(peak)}$ for ports P3, P4, P5, P6, P7, P8_0 to P8_4, P12, and P13 must be 80mA max. The total $I_{OH(peak)}$ for ports P0, P1, and P2 must be –40mA max. The total $I_{OH(peak)}$ for ports P3, P4, P5, P12, and P13 must be –40mA max. The total $I_{OH(peak)}$ for ports P6, P7, and P8_0 to P8_4 must be –40mA max. The total $I_{OH(peak)}$ for ports P8_6, P8_7, P9, P10, P14_0, and P14_1 must be –40mA max. Set Average Output Current to 1/2 of peak. The total $I_{OH(peak)}$ for ports P8_6, P8_7, P9 , P10, P11, P14_0, and P14_1 must be –40mA max.
   As for 80-pin version, the total $I_{OL(peak)}$ for all ports and $I_{OH(peak)}$ must be 80mA. max. due to one V_{CC} and one V_{SS}.
4. There is no external connections for port P1_0 to P1_7, P4_4 to P4_7, P7_2 to P7_5 and P9_1 in 80-pin version.

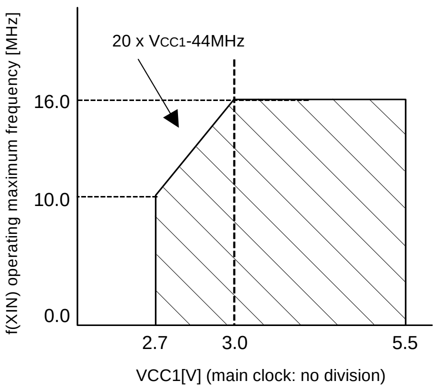
Table 5.3 Recommended Operating Conditions (2) (1)

Symbol	Parameter		Standard			Unit
			Min.	Typ.	Max.	
f(XIN)	Main Clock Input Oscillation Frequency (2)	V_{CC1}=3.0V to 5.5V	0		16	MHz
		V_{CC1}=2.7V to 3.0V	0		20×V_{CC1} −44	MHz
f(XCIN)	Sub-Clock Oscillation Frequency			32.768	50	kHz
f(Ring)	On-chip Oscillation Frequency		0.5	1	2	MHz
f(PLL)	PLL Clock Oscillation Frequency (2)	V_{CC1}=3.0V to 5.5V	10		24	MHz
		V_{CC1}=2.7V to 3.0V	10		46.67×V_{CC1} −116	MHz
f(BCLK)	CPU Operation Clock		0		24	MHz
t_{SU}(PLL)	PLL Frequency Synthesizer Stabilization Wait Time	V_{CC1}=5.5V			20	ms
		V_{CC1}=3.0V			50	ms

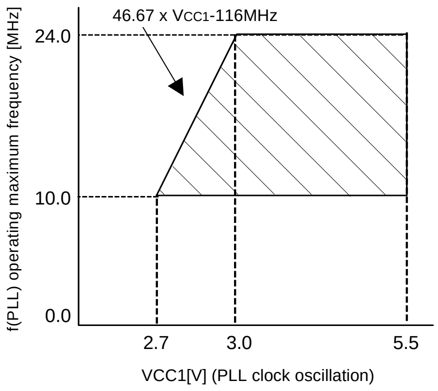
NOTES:

1. Referenced to V_{CC1} = V_{CC2} = 2.7 to 5.5V at T_{opr} = −20 to 85°C / −40 to 85°C unless otherwise specified.
2. Relationship between main clock oscillation frequency, and supply voltage.

Main clock input oscillation frequency

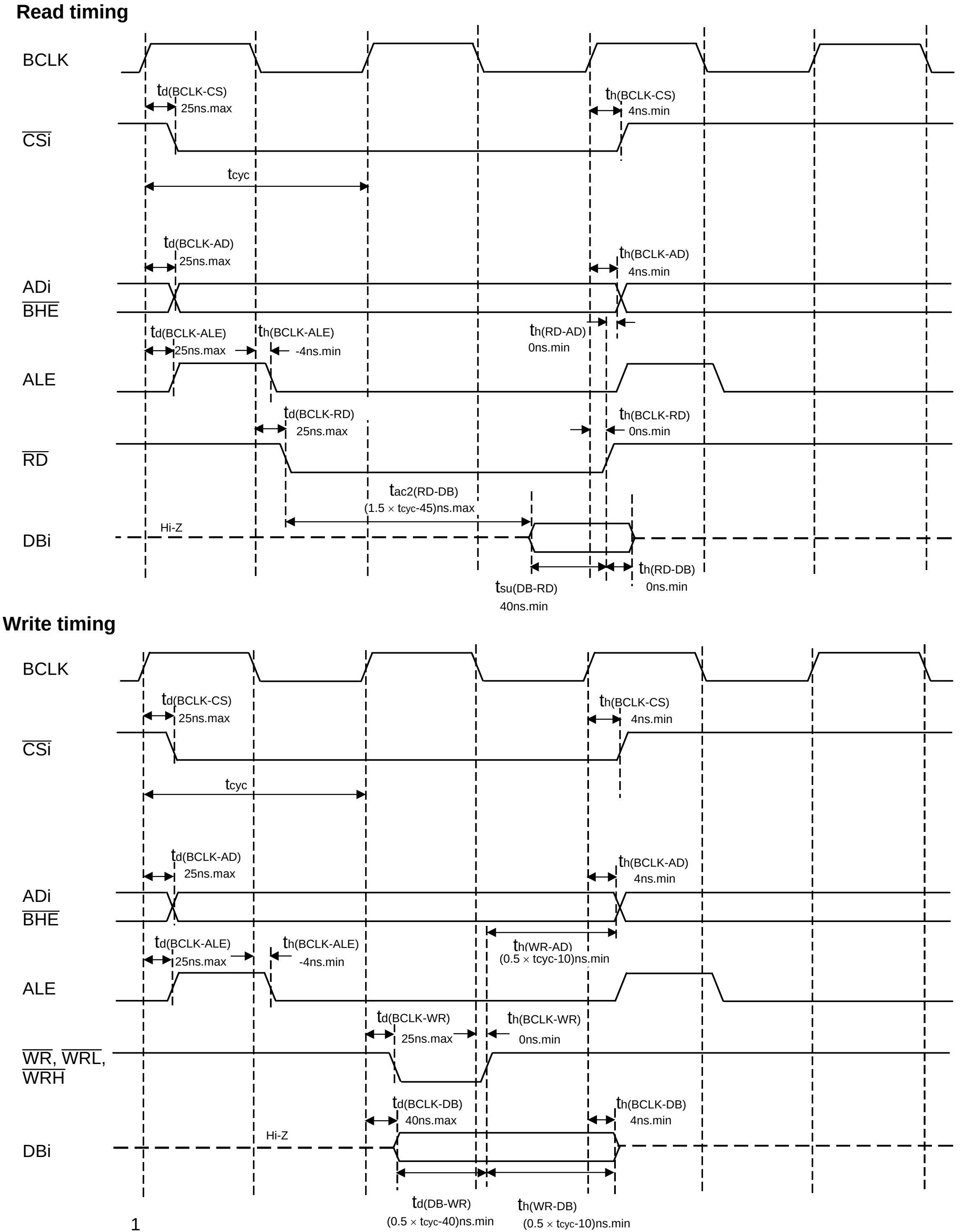


PLL clock oscillation frequency



$V_{CC1}=V_{CC2}=5V$

Memory Expansion Mode, Microprocessor Mode
(for 1-wait setting and external area access**)**



$$t_{cyc}=\frac{1}{f(BCLK)}$$

Measuring conditions
- $V_{CC1}=V_{CC2}=5V$
- Input timing voltage : $V_{IL}=0.8V$, $V_{IH}=2.0V$
- Output timing voltage : $V_{OL}=0.4V$, $V_{OH}=2.4V$

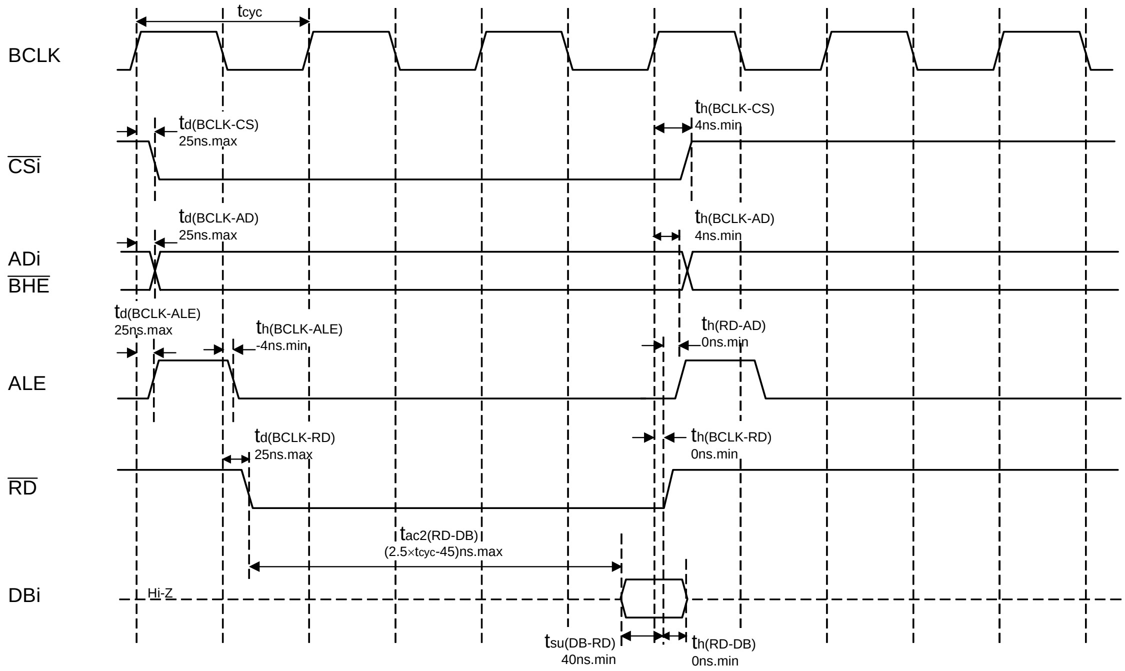
Figure 5.7 Timing Diagram (5)

$V_{CC1}=V_{CC2}=5V$

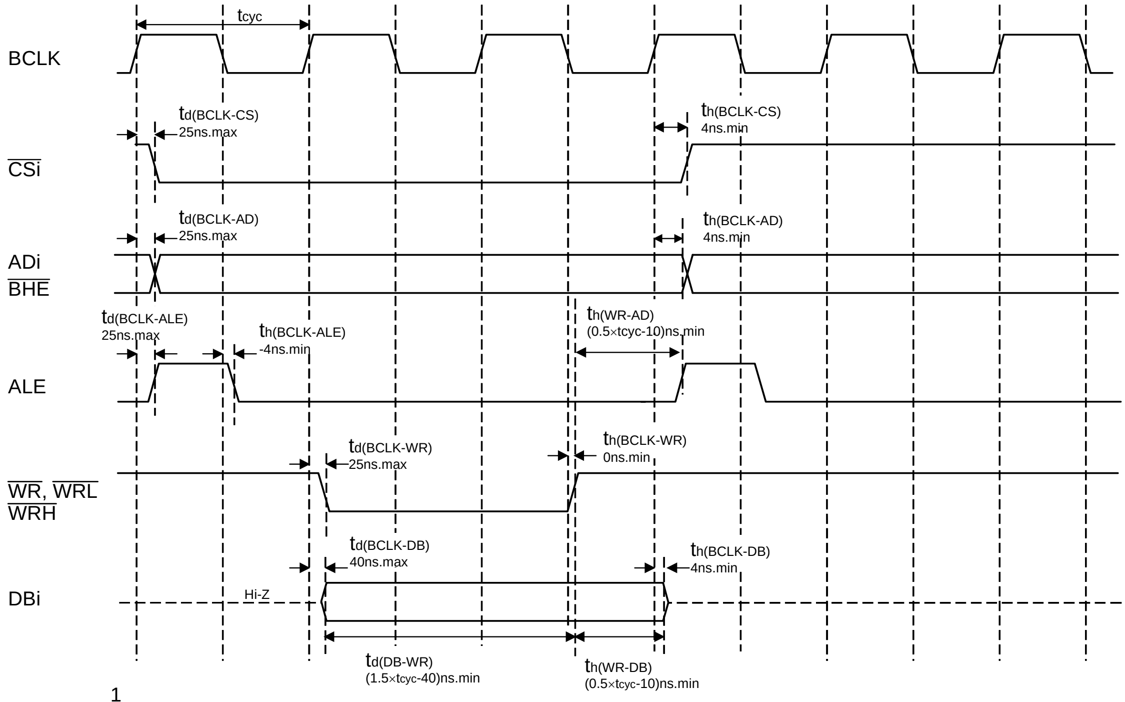
Memory Expansion Mode, Microprocessor Mode

(for 2-wait setting and external area access)

Read timing



Write timing



$T_{cyc}=\frac{1}{f(BCLK)}$

Measuring conditions
- · $V_{CC1}=V_{CC2}=5V$
- · Input timing voltage : $V_{IL}=0.8V$, $V_{IH}=2.0V$
- · Output timing voltage : $V_{OL}=0.4V$, $V_{OH}=2.4V$

Figure 5.8 Timing Diagram (6)

Timing Requirements
(V_{CC1} = V_{CC2} = 3V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.40 Timer B Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on one edge)	150		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on one edge)	60		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on one edge)	60		ns
$t_{c(TB)}$	TBiIN Input Cycle Time (counted on both edges)	300		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width (counted on both edges)	120		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width (counted on both edges)	120		ns

Table 5.41 Timer B Input (Pulse Period Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	600		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	300		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	300		ns

Table 5.42 Timer B Input (Pulse Width Measurement Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN Input Cycle Time	600		ns
$t_{w(TBH)}$	TBiIN Input HIGH Pulse Width	300		ns
$t_{w(TBL)}$	TBiIN Input LOW Pulse Width	300		ns

Table 5.43 A/D Trigger Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(AD)}$	$\overline{\text{ADTRG}}$ Input Cycle Time	1500		ns
$t_{w(ADL)}$	$\overline{\text{ADTRG}}$ Input LOW Pulse Width	200		ns

Table 5.44 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi Input Cycle Time	300		ns
$t_{w(CKH)}$	CLKi Input HIGH Pulse Width	150		ns
$t_{w(CKL)}$	CLKi Input LOW Pulse Width	150		ns
$t_{d(C-Q)}$	TXDi Output Delay Time		160	ns
$t_{h(C-Q)}$	TXDi Hold Time	0		ns
$t_{su(D-C)}$	RXDi Input Setup Time	100		ns
$t_{h(C-D)}$	RXDi Input Hold Time	90		ns

Table 5.45 External Interrupt $\overline{\text{INTi}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{\text{INTi}}$ Input HIGH Pulse Width	380		ns
$t_{w(INL)}$	$\overline{\text{INTi}}$ Input LOW Pulse Width	380		ns

$V_{CC1}=V_{CC2}=3V$

Switching Characteristics
(V_{CC1} = V_{CC2} = 3V, V_{SS} = 0V, at T_{opr} = –20 to 85°C / –40 to 85°C unless otherwise specified)

Table 5.46 Memory Expansion and Microprocessor Modes (for setting with no wait)

Symbol	Parameter		Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address Output Delay Time	See **Figure 5.12**		30	ns
$t_{h(BCLK-AD)}$	Address Output Hold Time (in relation to BCLK)		4		ns
$t_{h(RD-AD)}$	Address Output Hold Time (in relation to RD)		0		ns
$t_{h(WR-AD)}$	Address Output Hold Time (in relation to WR)		(NOTE 2)		ns
$t_{d(BCLK-CS)}$	Chip Select Output Delay Time			30	ns
$t_{h(BCLK-CS)}$	Chip Select Output Hold Time (in relation to BCLK)		4		ns
$t_{d(BCLK-ALE)}$	ALE Signal Output Delay Time			25	ns
$t_{h(BCLK-ALE)}$	ALE Signal Output Hold Time		–4		ns
$t_{d(BCLK-RD)}$	RD Signal Output Delay Time			30	ns
$t_{h(BCLK-RD)}$	RD Signal Output Hold Time		0		ns
$t_{d(BCLK-WR)}$	WR Signal Output Delay Time			30	ns
$t_{h(BCLK-WR)}$	WR Signal Output Hold Time		0		ns
$t_{d(BCLK-DB)}$	Data Output Delay Time (in relation to BCLK)			40	ns
$t_{h(BCLK-DB)}$	Data Output Hold Time (in relation to BCLK) (3)		4		ns
$t_{d(DB-WR)}$	Data Output Delay Time (in relation to WR)		(NOTE 1)		ns
th(WR-DB)	Data Output Hold Time (in relation to WR) (3)		(NOTE 2)		ns
$t_{d(BCLK-HLDA)}$	HLDA Output Delay Time			40	ns

NOTES:

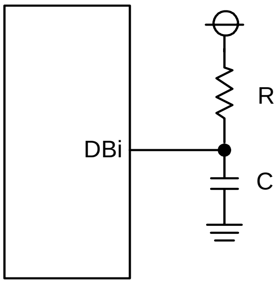
1. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^9}{f(BCLK)} - 40[ns] \qquad \text{f(BCLK) is 12.5MHz or less.}$$

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times10^9}{f(BCLK)} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
   Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
   Hold time of data bus is expressed in
   $t = -CR \times \ln(1 - V_{OL} / V_{CC2})$
   by a circuit of the right figure.
   For example, when V_{OL} = 0.2V_{CC2}, C = 30pF, R = 1kΩ, hold time of output "L" level is
   $t = -30pF \times 1k\Omega \times \ln(1 - 0.2V_{CC2} / V_{CC2})$
   $= 6.7ns.$



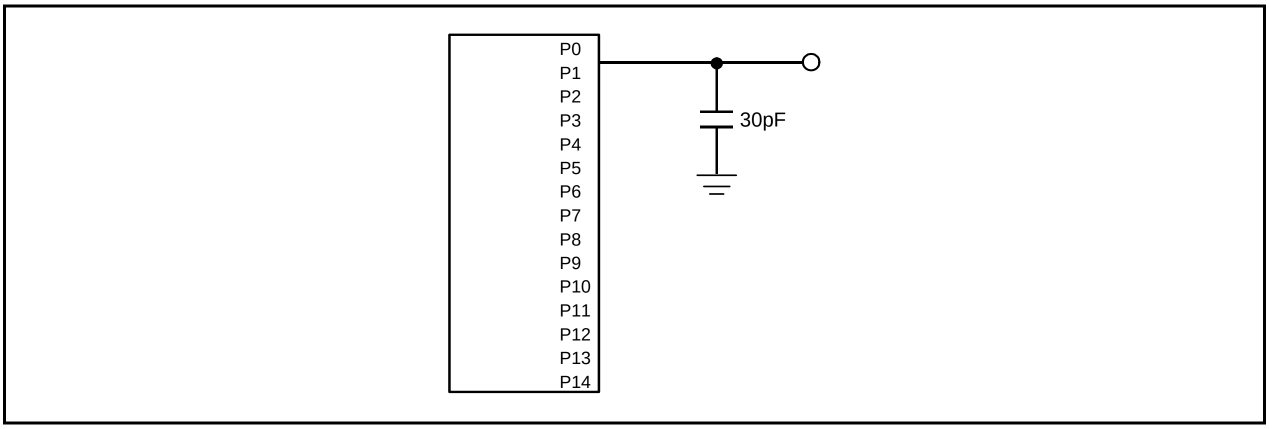


Figure 5.12 Ports P0 to P14 Measurement Circuit

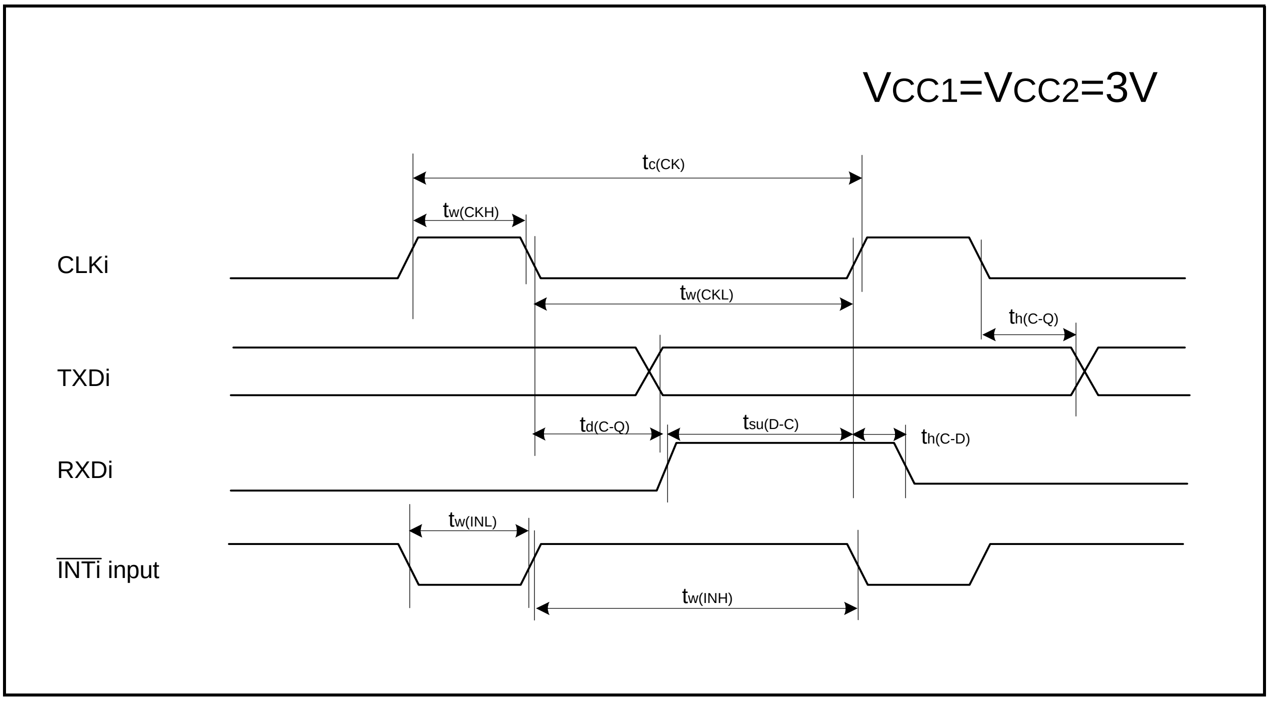
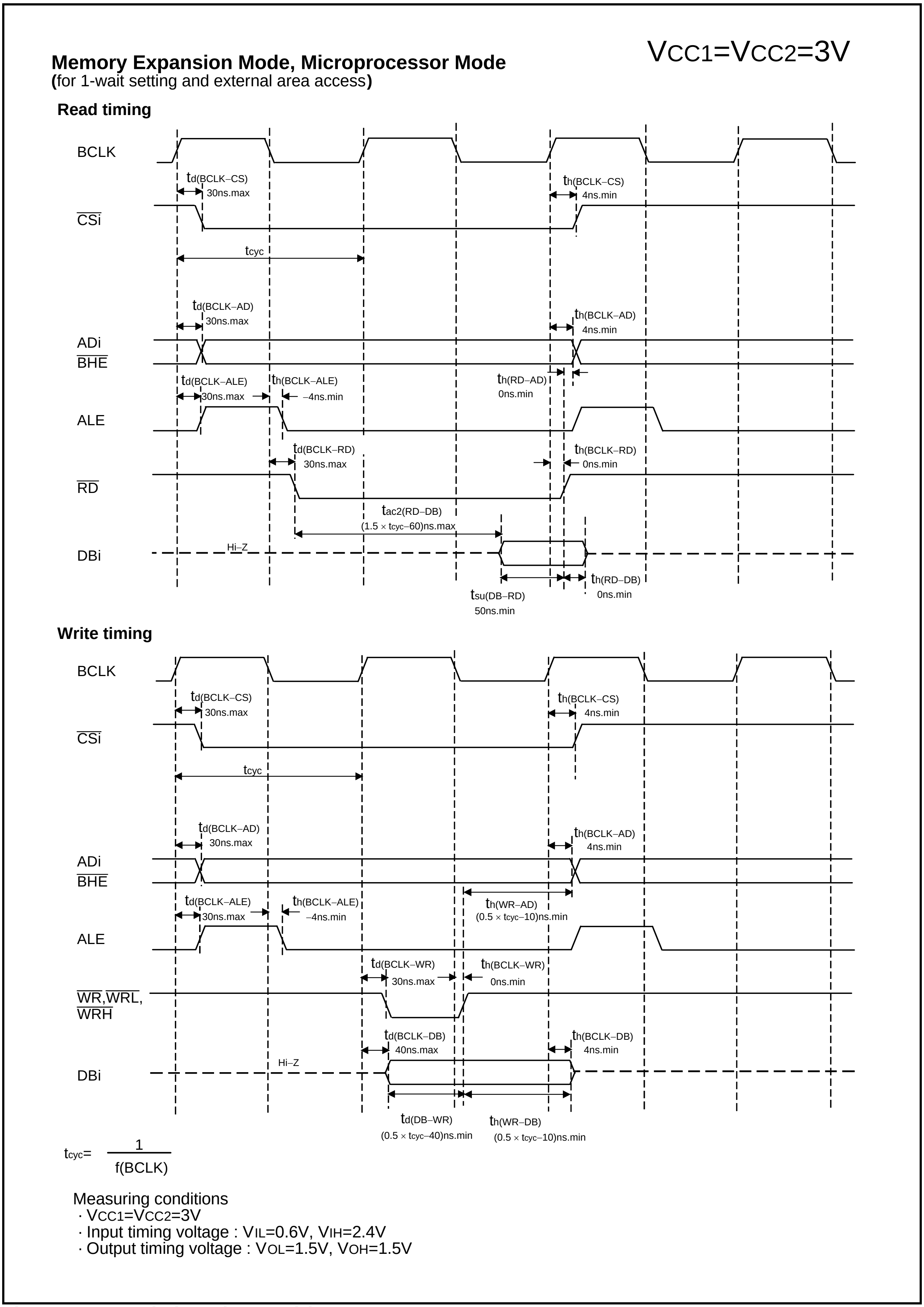


Figure 5.14 Timing Diagram (2)



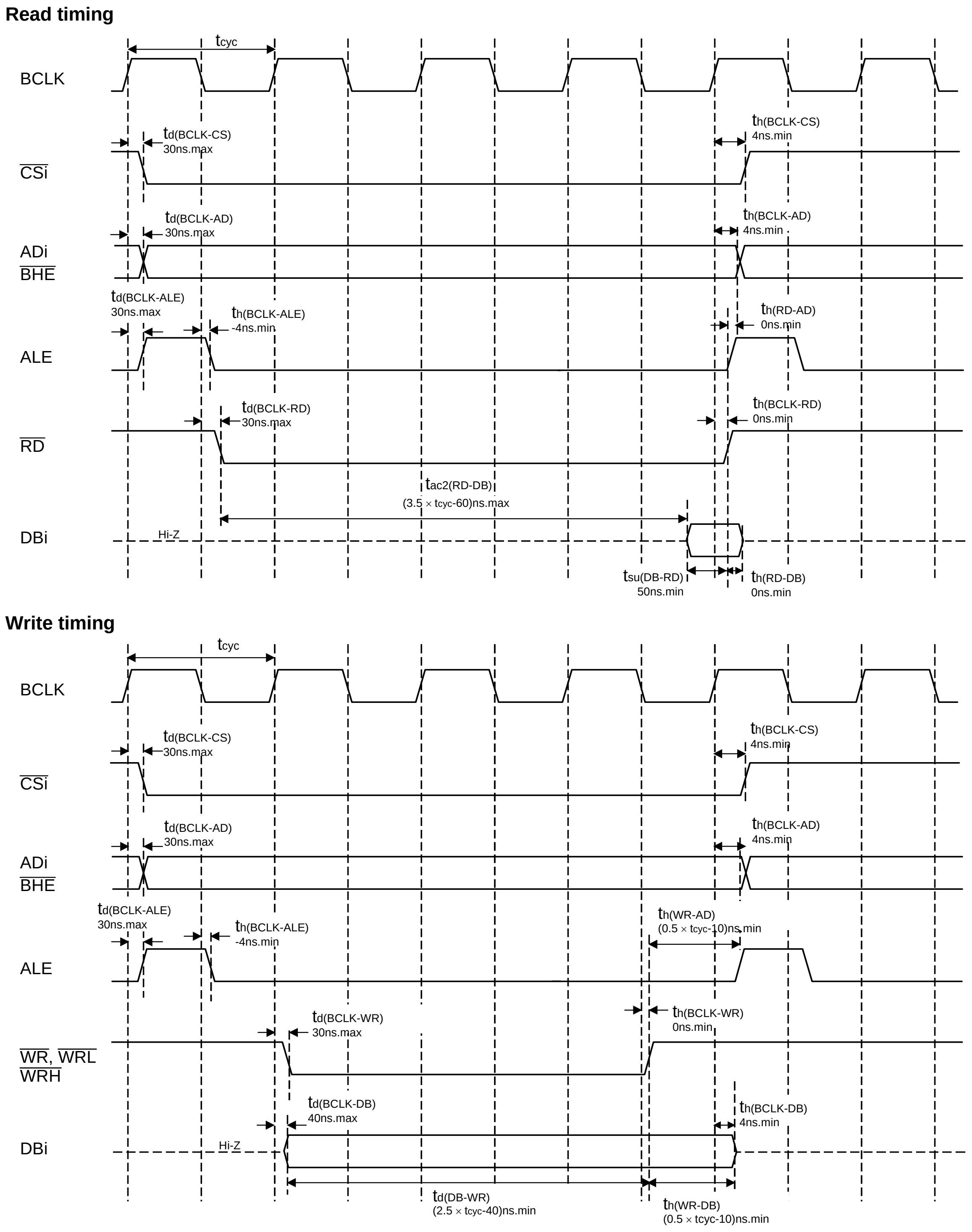
$$t_{cyc} = \frac{1}{f(BCLK)}$$

Measuring conditions
- $V_{CC1}=V_{CC2}=3V$
- Input timing voltage : $V_{IL}=0.6V$, $V_{IH}=2.4V$
- Output timing voltage : $V_{OL}=1.5V$, $V_{OH}=1.5V$

Figure 5.17 Timing Diagram (5)

$V_{CC1} = V_{CC2} = 3V$

Memory Expansion Mode, Microprocessor Mode
(for 3-wait setting and external area access**)**



$$t_{cyc} = \frac{1}{f(BCLK)}$$

Measuring conditions
- $V_{CC1}=V_{CC2}=3V$
- Input timing voltage : $V_{IL}=0.6V$, $V_{IH}=2.4V$
- Output timing voltage : $V_{OL}=1.5V$, $V_{OH}=1.5V$

Figure 5.19 Timing Diagram (7)

$V_{CC1}=V_{CC2}=5V$

Switching Characteristics
(V_{CC1} = V_{CC2} = 5V, V_{SS} = 0V, at T_{opr} = –40 to 85°C (T version) / –40 to 125°C (V version) unless otherwise specified)

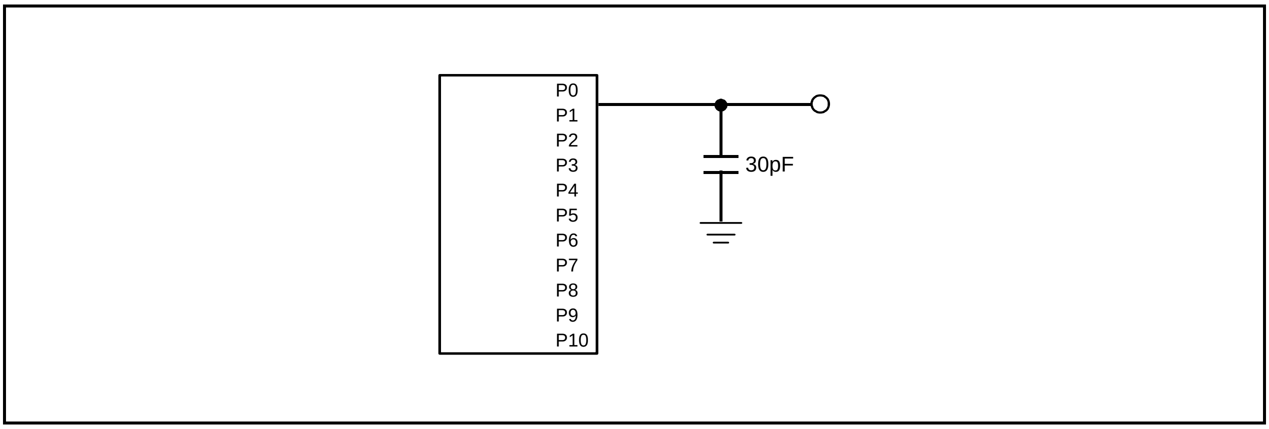


Figure 5.23 Ports P0 to P10 Measurement Circuit

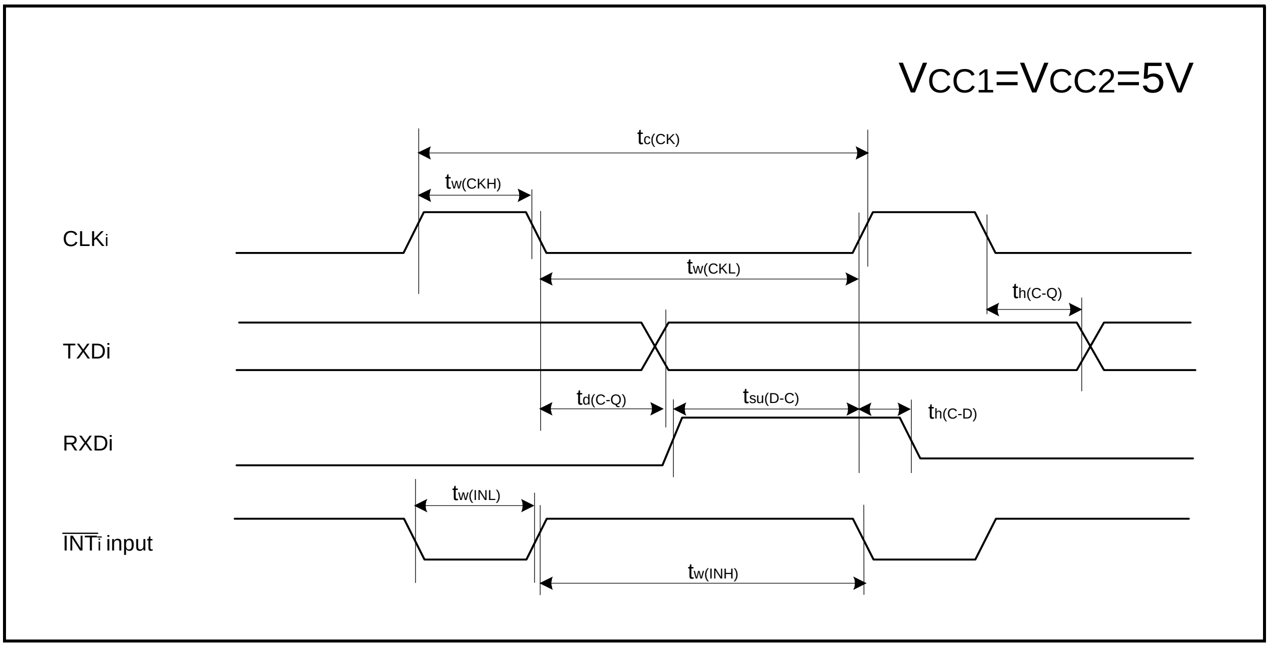


Figure 5.25 Timing Diagram (2)

Rev.	Date	Description	
		Page	Summary
		40	Table 5.24 is partly revised.
		57	Table 5.43 is partly revised.
		70	Table 5.48 is partly revised.
		72	Table 5.50 is partly revised.
		73	Table 5.53 is partly revised.
		74	Table 5.55 is revised.
		76	Table 5.57 is partly revised.
		79	Table 5.69 is partly revised.
2.41	Jan 01, 2006	-	voltage down detection reset -> brown-out detection Reset
		2-4	Tables 1.1 to 1.3 Performance outline of M16C/62P group are partly revised.
		7	Table 1.4 Product List (1) is partly revised. Note 1 is added.
		8	Table 1.5 Product List (2) is partly revised. Note 1, 2 and 3 are added.
		9	Table 1.6 Product List (3) is partly revised. Note 1 and 2 are added.
		10	Table 1.7 Product List (4) is partly revised. Note 1 and 2 are added.
		11	Figure 1.3 Type No., Memory Size, Shows RAM capacity, and Package is partly revised
		12	Table 1.8 Product Code of Flash Memory version and ROMless version for M16C/62P is partly revised.
		13	Table 1.9 Product Code of Flash Memory version for M16C/62P is partly revised.
		14	Figure 1.6 Pin Configuration (Top View) is partly revised.
		15-17	Tables 1.10 to 1.12 Pin Characteristics for 128-Pin Package are added.
		18-19	Figure 1.7 and 1.8 Pin Configuration (Top View) are partly revised.
		20-21	Tables 1.13 to 1.14 Pin Characteristics for 100-Pin Package are added.
		22	Figure 1.9 Pin Configuration (Top View) is partly revised.
		23-24	Tables 1.15 to 1.16 Pin Characteristics for 80-Pin Package are added.
		25-29	Tables 1.17 to 1.21 are partly revised.
		34	Note 4 of Table 4.1 SFR Information is partly revised.
		43	Table 5.4 A/D Conversion Characteristics is partly revised.
		45	Table 5.6 Flash Memory Version Electrical Characteristics for 100 cycle products is partly revised.
			Table 5.7 Flash Memory Version Electrical Characteristics for 10,000 cycle products is partly revised.
			Table 5.8 Flash Memory Version Program / Erase Voltage and Read Operation Voltage Characteristics is partly revised.
		46	Table 5.9 Low Voltage Detection Circuit Electrical Characteristics is partly revised.

REVISION HISTORY	M16C/62P Group (M16C/62P, M16C/62PT) Hardware Manual

Rev.	Date	Description	
		Page	Summary
		47	Figure 5.1 Power Supply Circuit Timing Diagram is partly revised.
		48	Table 5.11 Electrical Characteristics (1) is partly deleted.
		49	Table 5.12 Electrical Characteristics (2) is partly revised.
		50	Note 1 of Table 5.13 External Clock Input (XIN input) is added.
		67	Notes 1 to 4 of Table 5.32 External Clock Input (XIN input) are added.
		85	Table 5.53 Flash Memory Version Electrical Characteristics for 100 cycle products is partly revised. Standard (Min.) is partly revised. Table 5.54 Flash Memory Version Electrical Characteristics for 10,000 cycle products is partly revised. Standard (Min.) is partly revised. Note 5 is revised. Table 23.55 Flash Memory Version Program / Erase Voltage and Read Operation Voltage Characteristics is partly revised.
		87	Table 5.57 Electrical Characteristics (1) is partly deleted.
		88	Table 5.58 Electrical Characteristics is partly revised.

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Keep safety first in your circuit designs!
1. Renesas Technology Corp. puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.
Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials
1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corp. product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corp. or a third party.
2. Renesas Technology Corp. assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corp. without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor for the latest product information before purchasing a product listed herein.
The information described here may contain technical inaccuracies or typographical errors.
Renesas Technology Corp. assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
Please also pay attention to information published by Renesas Technology Corp. by various means, including the Renesas Technology Corp. Semiconductor home page (http://www.renesas.com).
4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corp. assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
5. Renesas Technology Corp. semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Renesas Technology Corp. or an authorized Renesas Technology Corp. product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
6. The prior written approval of Renesas Technology Corp. is necessary to reprint or reproduce in whole or in part these materials.
7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
8. Please contact Renesas Technology Corp. for further details on these materials or the products contained therein.

RENESAS SALES OFFICES

http://www.renesas.com

Refer to "**http://www.renesas.com/en/network**" for the latest and detailed information.

Renesas Technology America, Inc.
450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.
10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.
Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.
Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510

© 2006. Renesas Technology Corp., All rights reserved. Printed in Japan.

Colophon .3.0